

Supplementary materials

Enhanced thermoelectric performance in $\text{In}_{1-x}\text{Ga}_x\text{Sb}$ originating from scattering of point defect and nanoinclusion

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For testing the reproducibility of TE properties, the sample of $\text{In}_{0.9}\text{Ga}_{0.1}\text{Sb}$, which has the best thermoelectric performance in our experiment, is kept at 650 K for 48h and then retested for 3 times. Here we show the retested results in Fig. S1 to Fig. S5.

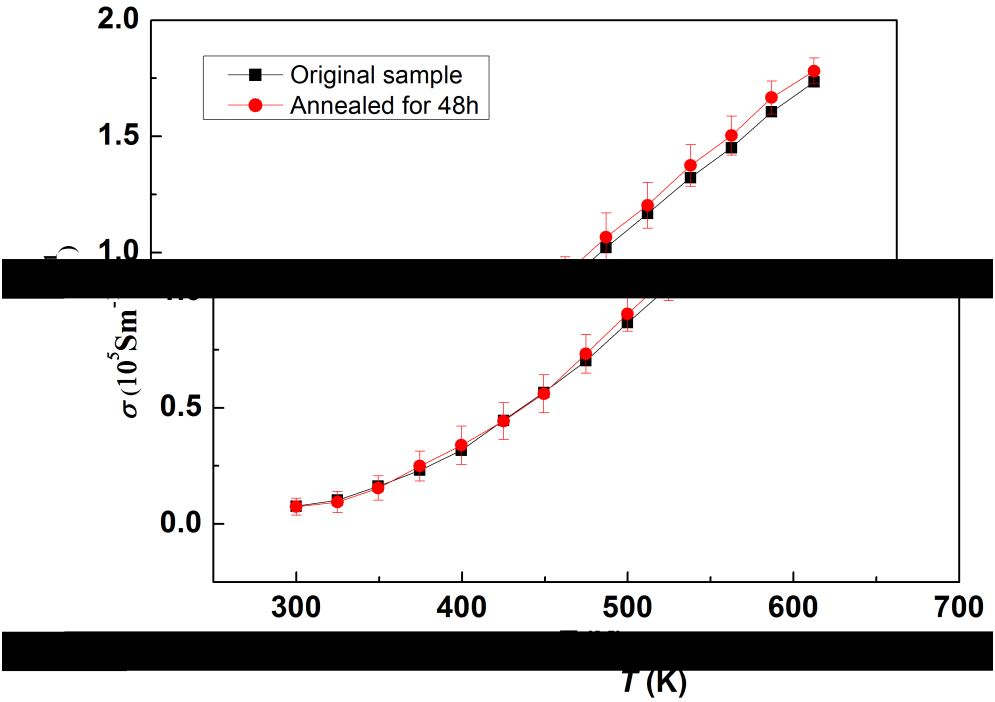


Fig. S1. Temperature dependence of electrical conductivities for $\text{In}_{0.9}\text{Ga}_{0.1}\text{Sb}$

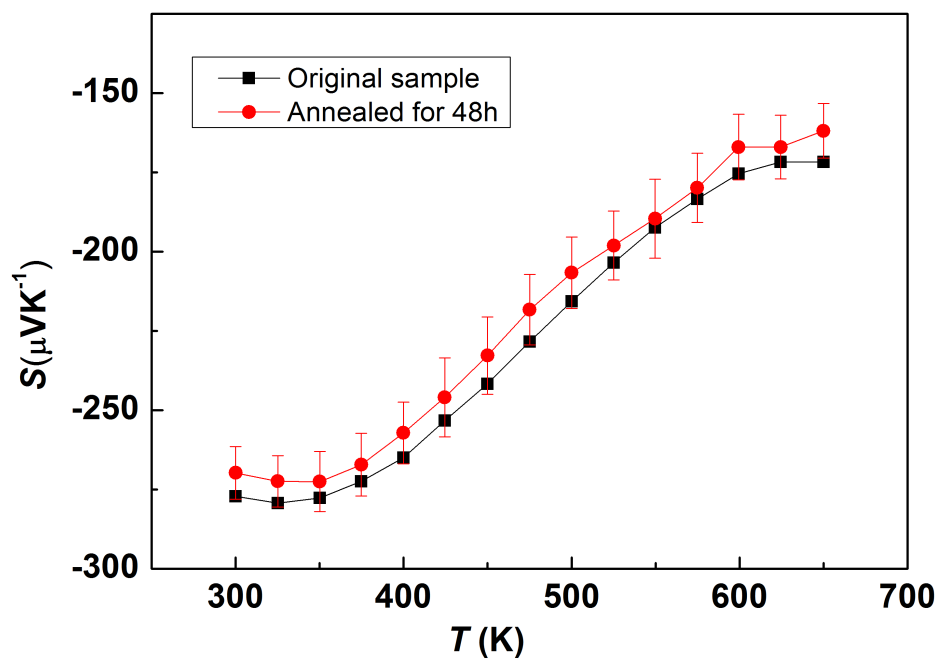


Fig. S2. Temperature dependence of Seebeck coefficients for $\text{In}_{0.9}\text{Ga}_{0.1}\text{Sb}$

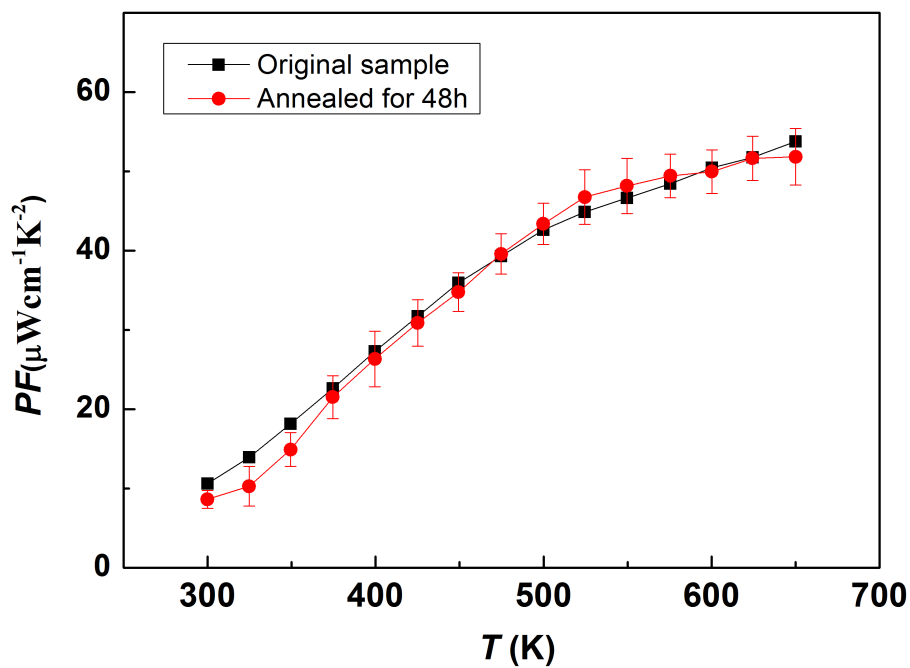


Fig. S3. Temperature dependence of the Power Factors for $\text{In}_{0.9}\text{Ga}_{0.1}\text{Sb}$

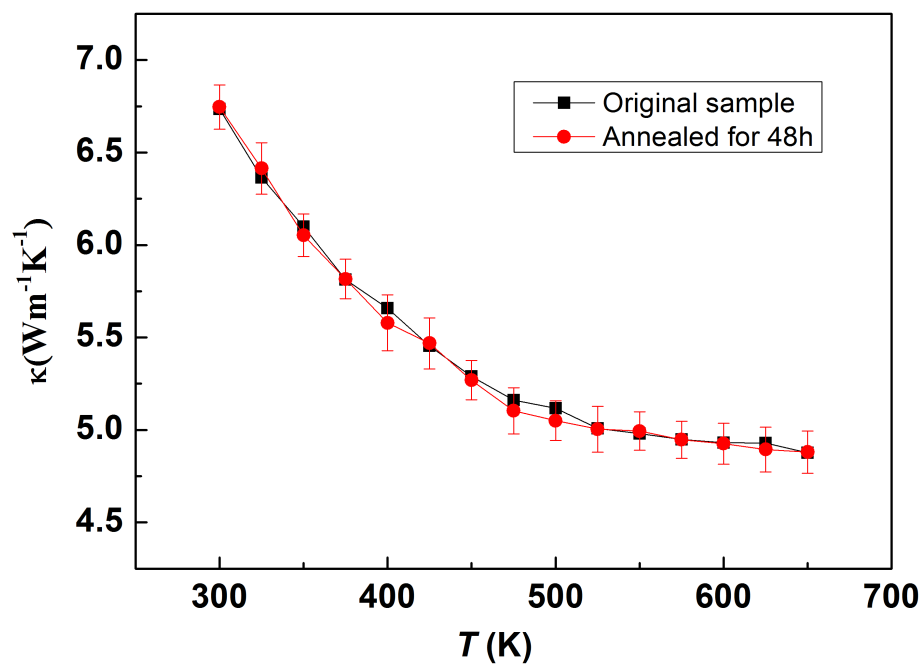


Fig. S4. Temperature dependence of thermal conductivities for $\text{In}_{0.9}\text{Ga}_{0.1}\text{Sb}$

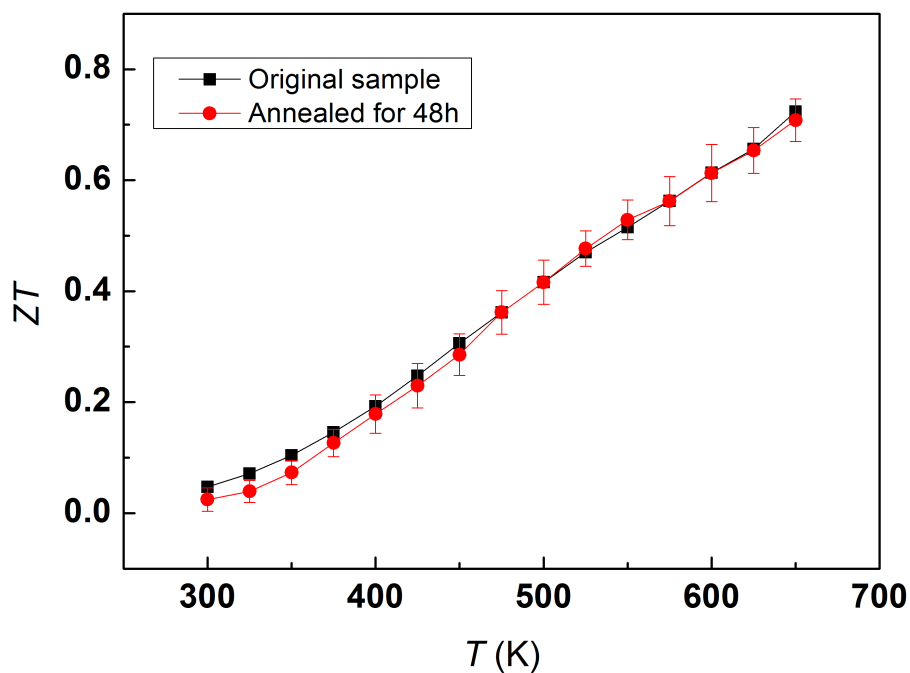


Fig. S5. Temperature dependence of ZT values for $\text{In}_{0.9}\text{Ga}_{0.1}\text{Sb}$